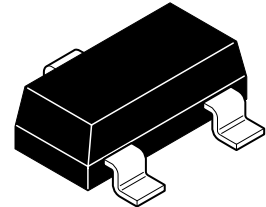


# ZXTN25060BFH

## 60V, SOT23, NPN medium power transistor

### Summary

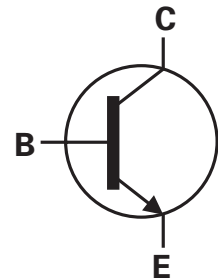
$BV_{CEX} > 150V$   
 $BV_{CEO} > 60V$   
 $BV_{ECO} > 6V$   
 $I_{C(cont)} = 3.5A$   
 $V_{CE(sat)} < 65\text{ mV @ } 1A$   
 $R_{CE(sat)} = 43\text{ m}\Omega$   
 $P_D = 1.25W$



Complementary part number ZXTP25060BFH

### Description

Advanced process capability and package design have been used to maximize the power handling and performance of this small outline transistor. The compact size and ratings of this device make it ideally suited to applications where space is at a premium.

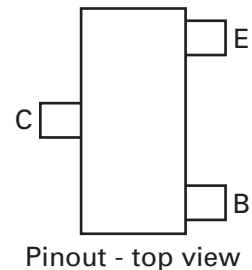


### Features

- High power dissipation SOT23 package
- High peak current
- Low saturation voltage
- 150V forward blocking voltage

### Applications

- Lamp, relay and solenoid drivers
- General switching in automotive and industrial applications
- Motor drive and control



### Ordering information

Device	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTN25060BFHTA	7	8	3,000

### Device marking

019

# ZXTN25060BFH

## Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Collector-base voltage	$V_{CBO}$	150	V
Collector-emitter voltage (forward blocking)	$V_{CEX}$	150	V
Collector-emitter voltage	$V_{CEO}$	60	V
Emitter-collector voltage (reverse blocking)	$V_{ECO}$	6	V
Emitter-base voltage	$V_{EBO}$	7	V
Continuous collector current <sup>(b)</sup>	$I_C$	3.5	A
Peak pulse current	$I_{CM}$	10	A
Power dissipation at $T_A = 25^\circ\text{C}$ <sup>(a)</sup> Linear derating factor	$P_D$	0.73 5.84	W mW/°C
Power dissipation at $T_A = 25^\circ\text{C}$ <sup>(b)</sup> Linear derating factor	$P_D$	1.05 8.4	W mW/°C
Power dissipation at $T_A = 25^\circ\text{C}$ <sup>(c)</sup> Linear derating factor	$P_D$	1.25 9.6	W mW/°C
Power dissipation at $T_A = 25^\circ\text{C}$ <sup>(d)</sup> Linear derating factor	$P_D$	1.81 14.5	W mW/°C
Operating and storage temperature range	$T_j, T_{stg}$	- 55 to 150	°C

## Thermal resistance

Parameter	Symbol	Limit	Unit
Junction to ambient <sup>(a)</sup>	$R_{\theta JA}$	171	°C/W
Junction to ambient <sup>(b)</sup>	$R_{\theta JA}$	119	°C/W
Junction to ambient <sup>(c)</sup>	$R_{\theta JA}$	100	°C/W
Junction to ambient <sup>(d)</sup>	$R_{\theta JA}$	69	°C/W

### NOTES:

(a) For a device surface mounted on 15mm x 15mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

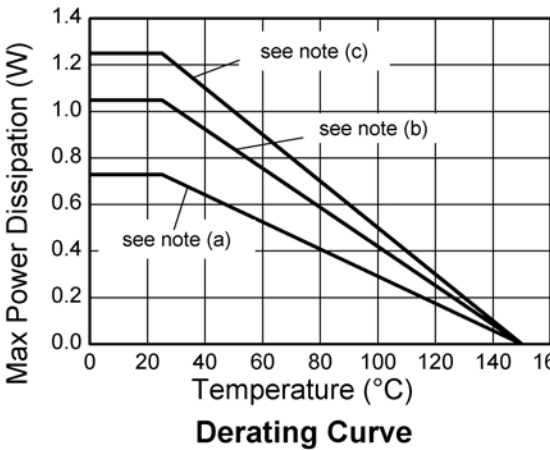
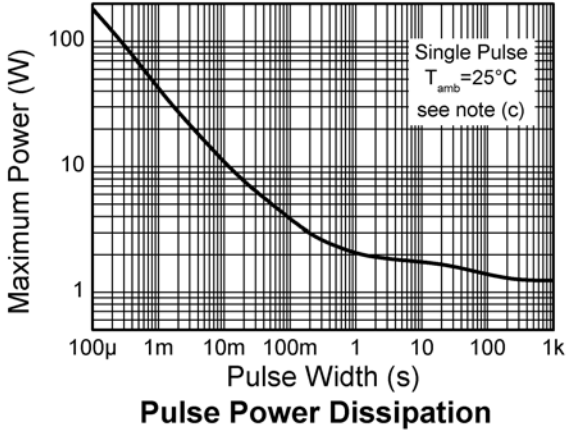
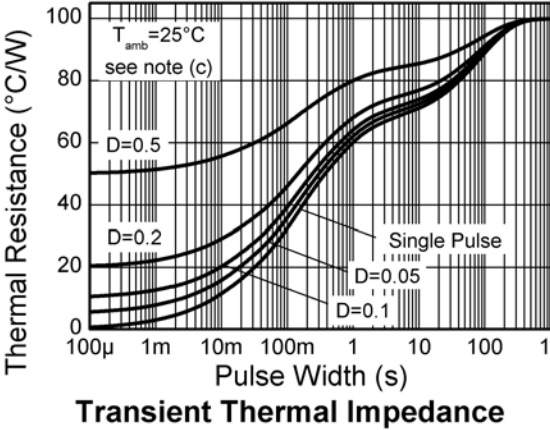
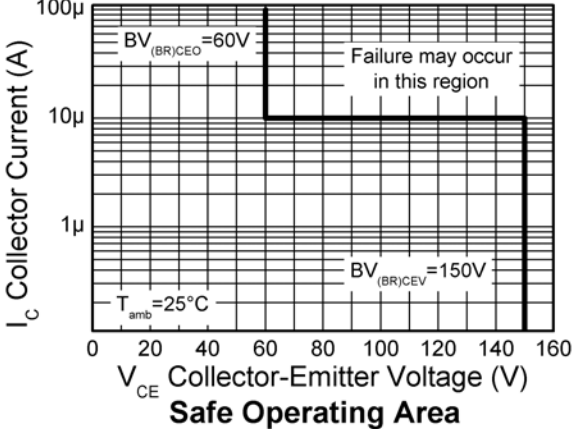
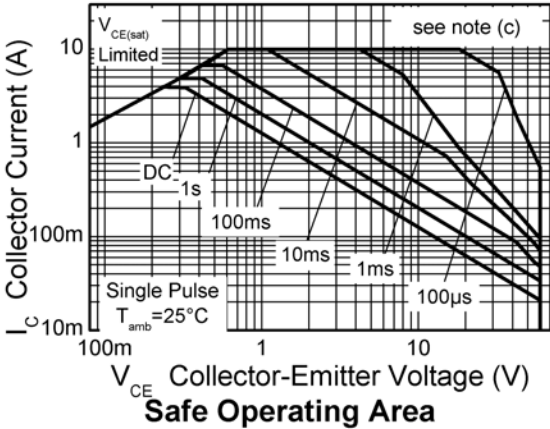
(b) Mounted on 25mm x 25mm x 1.6mm FR4 PCB with a high coverage of single sided 2 oz copper in still air conditions.

(c) Mounted on 50mm x 50mm x 1.6mm FR4 PCB with a high coverage of single sided 2 oz copper in still air conditions.

(d) As (c) above measured at  $t < 5$ secs.

# ZXTN25060BFH

## Characteristics



# ZXTN25060BFH

## ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated)

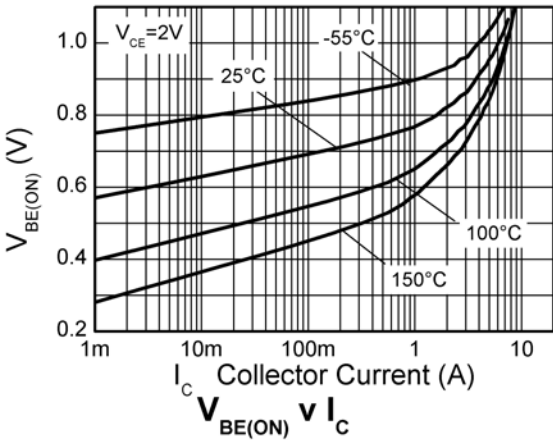
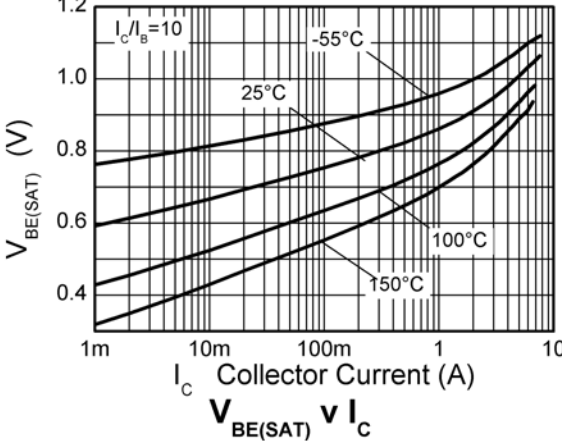
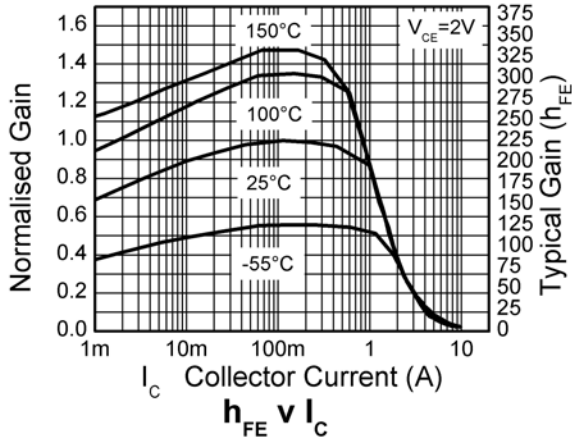
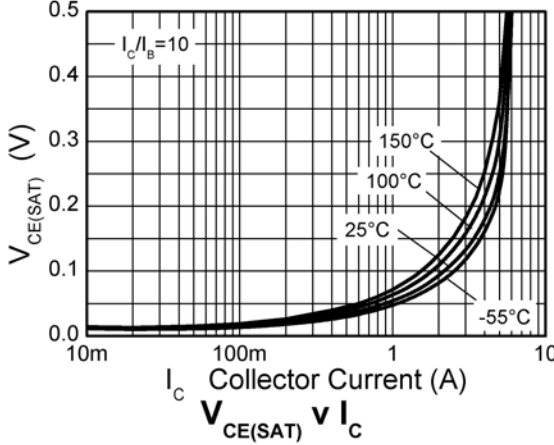
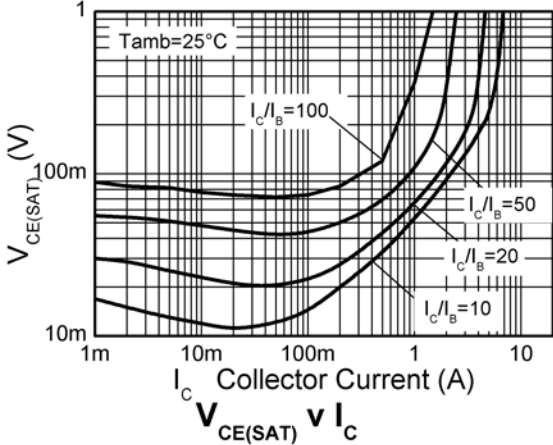
Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	$BV_{CBO}$	150	190		V	$I_C = 100\mu\text{A}$
Collector-emitter breakdown voltage (forward blocking)	$BV_{CEX}$	150	190			$I_C = 100\mu\text{A}$ , $R_{BE} \leq 1\text{k}\Omega$ or $-1\text{V} < V_{BE} < 0.25\text{V}$
Collector-emitter breakdown voltage (base open)	$BV_{CEO}$	60	80		V	$I_C = 10\text{mA}$ (*)
Emitter-collector breakdown voltage (reverse blocking)	$BV_{ECX}$	6	8		V	$I_E = 100\mu\text{A}$ , $R_{BC} \leq 1\text{k}\Omega$ or $0.25\text{V} > V_{BC} > -0.25\text{V}$
Emitter-collector breakdown voltage (base open)	$BV_{ECO}$	6	7		V	$I_E = 100\mu\text{A}$ ,
Emitter-base breakdown voltage	$BV_{EBO}$	7	8		V	$I_E = 100\mu\text{A}$
Collector cut-off current	$I_{CBO}$		<1	50 20	nA $\mu\text{A}$	$V_{CB} = 120\text{V}$ $V_{CB} = 120\text{V}$ , $T_{amb} = 100^{\circ}\text{C}$
Collector-emitter cut-off current	$I_{CEX}$		-	100	nA	$V_{CE} = 120\text{V}$ ; $R_{BE} \leq 1\text{k}\Omega$ or $-1\text{V} < V_{BE} < 0.25\text{V}$
Emitter cut-off current	$I_{EBO}$		<1	50	nA	$V_{EB} = 5.6\text{V}$
Collector-emitter saturation voltage	$V_{CE(sat)}$		33	40	mV	$I_C = 0,5\text{A}$ , $I_B = 50\text{mA}$ (*)
			73	95	mV	$I_C = 0,5\text{A}$ , $I_B = 10\text{mA}$ (*)
			50	65	mV	$I_C = 1\text{A}$ , $I_B = 100\text{mA}$ (*)
			150	175	mV	$I_C = 3.5\text{A}$ , $I_B = 350\text{mA}$ (*)
Base-emitter saturation voltage	$V_{BE(sat)}$		960	1050	mV	$I_C = 3.5\text{A}$ , $I_B = 350\text{mA}$ (*)
Base-emitter turn-on voltage	$V_{BE(on)}$		865	950	mV	$I_C = 3.5\text{A}$ , $V_{CE} = 2\text{V}$ (*)
Static forward current transfer ratio	$h_{FE}$	100	200	300		$I_C = 10\text{mA}$ , $V_{CE} = 2\text{V}$ (*)
		90	180			$I_C = 1\text{A}$ , $V_{CE} = 2\text{V}$ (*)
		25	40			$I_C = 3.5\text{A}$ , $V_{CE} = 2\text{V}$ (*)
Transition frequency	$f_T$		185		MHz	$I_C = 100\text{mA}$ , $V_{CE} = 5\text{V}$ $f = 100\text{MHz}$
Output capacitance	$C_{OBO}$		11.5	20	pF	$V_{CB} = 10\text{V}$ , $f = 1\text{MHz}$ (*)
Turn-on time	$t_{(on)}$		34		ns	$V_{CC} = 10\text{V}$ . $I_C = 500\text{mA}$ ,
Turn-off time	$t_{(off)}$		566		ns	$I_{B1} = I_{B2} = 50\text{mA}$ .

### NOTES:

(\*) Measured under pulsed conditions. Pulse width  $\leq 300\mu\text{s}$ ; duty cycle  $\leq 2\%$ .

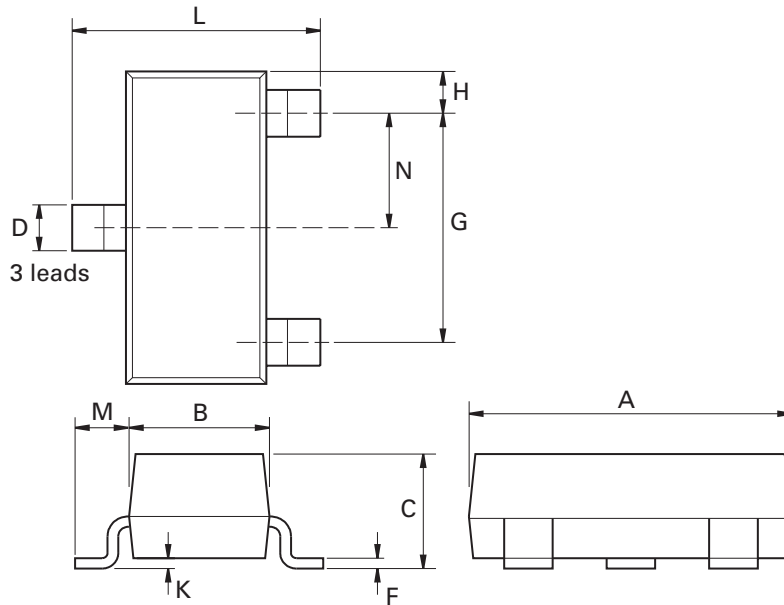
# ZXTN25060BFH

## Typical characteristics



# ZXTN25060BFH

## Package outline - SOT23



Dim.	Millimeters		Inches		Dim.	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Max.	Max.
A	2.67	3.05	0.105	0.120	H	0.33	0.51	0.013	0.020
B	1.20	1.40	0.047	0.055	K	0.01	0.10	0.0004	0.004
C	-	1.10	-	0.043	L	2.10	2.50	0.083	0.0985
D	0.37	0.53	0.015	0.021	M	0.45	0.64	0.018	0.025
F	0.085	0.15	0.0034	0.0059	N	0.95 NOM		0.0375 NOM	
G	1.90 NOM		0.075 NOM		-	-	-	-	-

**Note:** Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

Europe	Americas	Asia Pacific	Corporate Headquarters
Zetex GmbH Streitfeldstraße 19 D-81673 München Germany	Zetex Inc 700 Veterans Memorial Highway Hauppauge, NY 11788 USA	Zetex (Asia Ltd) 3701-04 Metroplaza Tower 1 Hing Fong Road, Kwai Fong Hong Kong	Zetex Semiconductors plc Zetex Technology Park, Chadderton Oldham, OL9 9LL United Kingdom
Telefon: (49) 89 45 49 49 0 Fax: (49) 89 45 49 49 49 europe.sales@zetex.com	Telephone: (1) 631 360 2222 Fax: (1) 631 360 8222 usa.sales@zetex.com	Telephone: (852) 26100 611 Fax: (852) 24250 494 asia.sales@zetex.com	Telephone: (44) 161 622 4444 Fax: (44) 161 622 4446 hq@zetex.com

For international sales offices visit [www.zetex.com/offices](http://www.zetex.com/offices)

Zetex products are distributed worldwide. For details, see [www.zetex.com/salesnetwork](http://www.zetex.com/salesnetwork)

This publication is issued to provide outline information only which (unless agreed by the company in writing) may not be used, applied or reproduced for any purpose or form part of any order or contact or be regarded as a representation relating to the products or services concerned. The company reserves the right to alter without notice the specification, design, price or conditions of supply of any product or service.



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



#### Как с нами связаться

**Телефон:** 8 (812) 309 58 32 (многоканальный)

**Факс:** 8 (812) 320-02-42

**Электронная почта:** [org@eplast1.ru](mailto:org@eplast1.ru)

**Адрес:** 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.